MOSFET – Power, Single N-Channel, SUPERFET® V, FRFET®, TO247-3L

600 V, 55 mΩ, 45 A

NVHL055N60S5F

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
600 V	55 mΩ @ 10 V	45 A

Description

The SUPERFET V MOSFET FRFET series has optimized body diode performance characteristics. This can allow for the removal of components in the application and improve application performance and reliability, particularly when soft switching topologies are used.

Features

- 650 V @ T_J = 150°C / Typ. $R_{DS(on)}$ = 44 mΩ
- 100% Avalanche Tested
- Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Electric Vehicle On Board Chargers
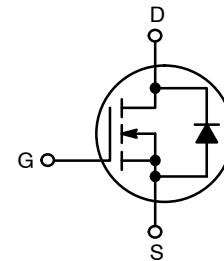- EV Main Battery DC/DC Converters

POWER MOSFET

**TO−247 Long Leads
CASE 340CX**

MARKING DIAGRAM

V055N
60S5F
AYWWZZ

V055N60S5F	= Specific Device Code
A	= Assembly Location
YWW	= Data Code (Year & Week)
ZZ	= Assembly Lot

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

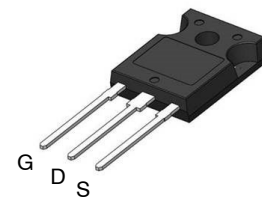| Parameter		Symbol	Value	Unit
Drain−to−Source Voltage		V_{DSS}	600	V
Gate−to−Source Voltage	DC	V_{GS}	±30	V
	AC (f > 1 Hz)		±30	
Continuous Drain Current	T_C = 25°C	I_D	45	A
	T_C = 100°C		28	
Power Dissipation	T_C = 25°C	P_D	278	W
Pulsed Drain Current	T_C = 25°C, t_P = 10 μs	I_{DM}	159	A
Pulsed Source Current (Body Diode)		I_{SM}	159	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +150	°C
Source Current (Body Diode)		I_S	45	A
Single Pulse Avalanche Energy	(I_L = 7 A, R_G = 25 Ω)	E_{AS}	417	mJ
Avalanche Current		I_{AS}	7	A
Repetitive Avalanche Energy (Note 1)		E_{AR}	2.78	mJ
MOSFET dv/dt		dvdt	120	V/ns
Peak Diode Recovery dv/dt (Note 2)			70	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Repetitive rating: pulse−width limited by maximum junction temperature.
2. I_{SD} ≤ 22.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

ORDERING INFORMATION

Device	Package	Shipping
NVHL055N60S5F	TO−247	30 Units / Tube

NVHL055N60S5F

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case, Max.	$R_{\theta JC}$	0.45	°C/W
Thermal Resistance, Junction−to−Ambient, Max.	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	600	–	–	V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 10 mA, Referenced to 25°C	–	581	–	mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 600 V, T_J = 25°C	–	–	10	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 22.5 A, T_J = 25°C	–	44	55	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 5.2 mA, T_J = 25°C	3.2	–	4.8	V
Forward Trans−conductance	g_{FS}	V_{DS} = 20 V, I_D = 22.5 A	–	44.8	–	S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{DS} = 400 V, V_{GS} = 0 V, f = 250 kHz	–	4603	–	pF
Output Capacitance	C_{OSS}		–	72.9	–	
Time Related Output Capacitance	$C_{OSS(tr.)}$	I_D = Constant, V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	1114	–	
Energy Related Output Capacitance	$C_{OSS(er.)}$	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	125	–	
Total Gate Charge	$Q_{G(tot)}$	V_{DD} = 400 V, I_D = 22.5 A, V_{GS} = 10 V	–	85.2	–	nC
Gate−to−Source Charge	Q_{GS}		–	26.2	–	
Gate−to−Drain Charge	Q_{GD}		–	24.9	–	
Gate Resistance	R_G	f = 1 MHz	–	4.32	–	Ω
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 0/10 V, V_{DD} = 400 V, I_D = 22.5 A, R_G = 4.7 Ω	–	44	–	ns
Rise Time	t_r		–	26.2	–	
Turn-Off Delay Time	$t_{d(off)}$		–	108	–	
Fall Time	t_f		–	2.6	–	
SOURCE-TO−DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_{SD} = 22.5 A, T_J = 25°C	–	–	1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, I_{SD} = 22.5 A, dI/dt = 100 A/μs, V_{DD} = 400 V	–	128	–	ns
Reverse Recovery Charge	Q_{RR}		–	758	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

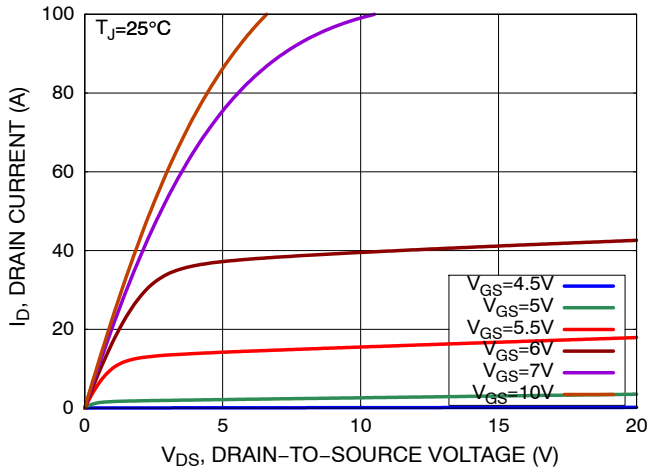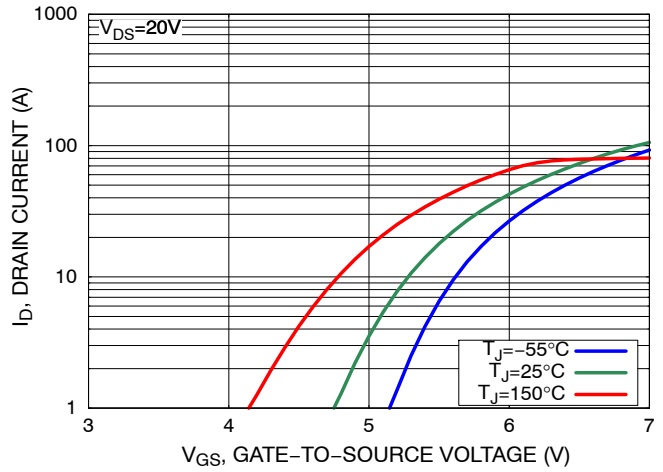**Figure 1. On−Region Characteristics**
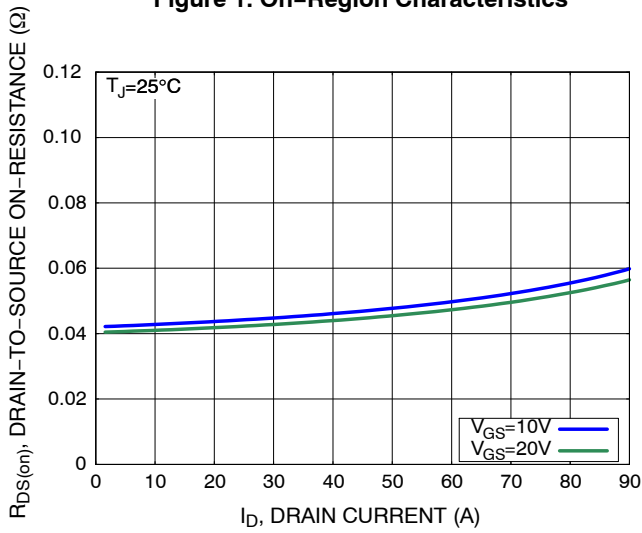
Figure 2. Transfer Characteristics

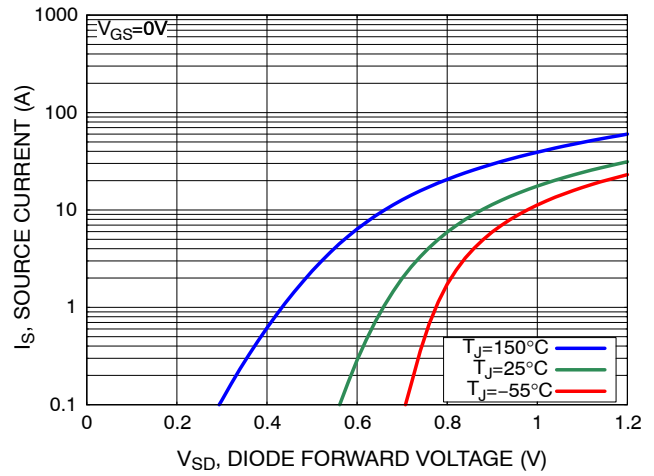**Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage**

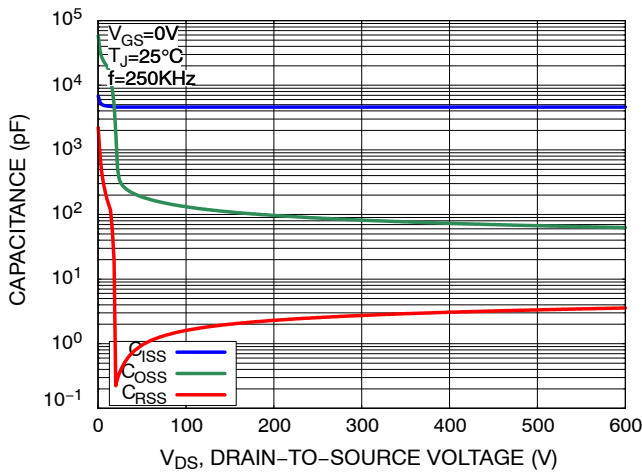**Figure 4. Diode Forward Voltage vs. Source Current**
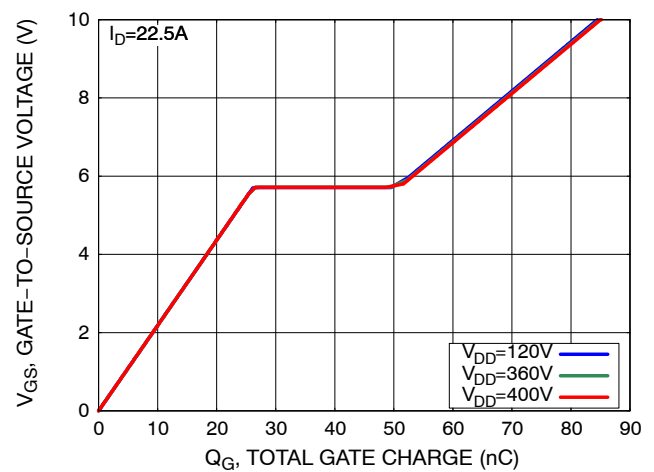
Figure 5. Capacitance Characteristics

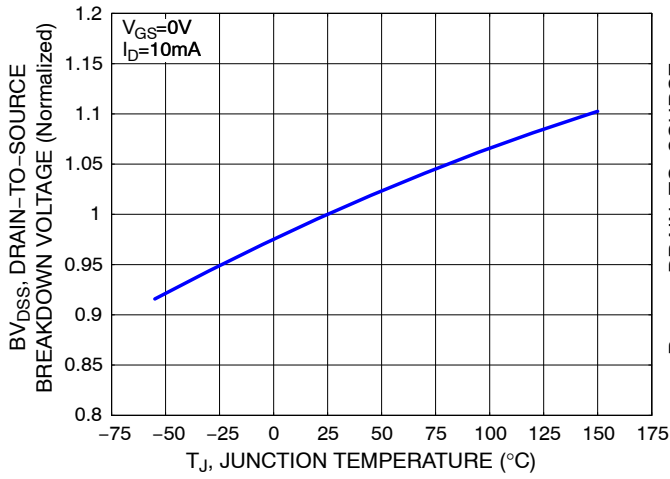**Figure 6. Gate Charge Characteristics**

TYPICAL CHARACTERISTICS
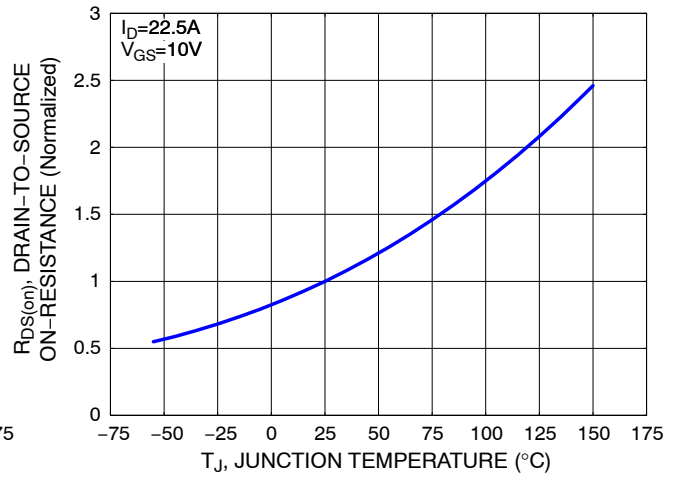

Figure 7. Breakdown Voltage Variation vs. Temperature
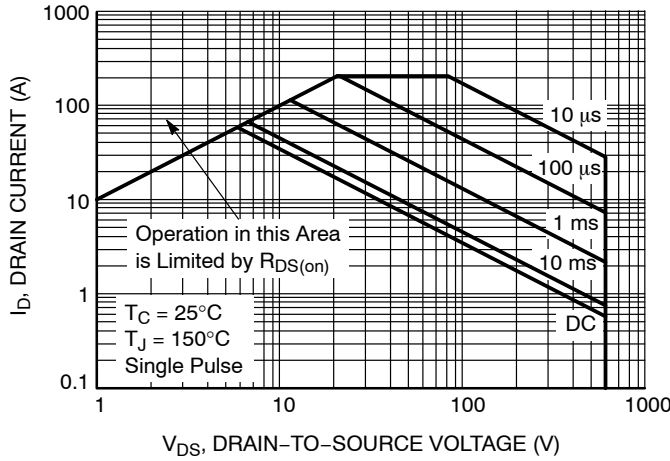

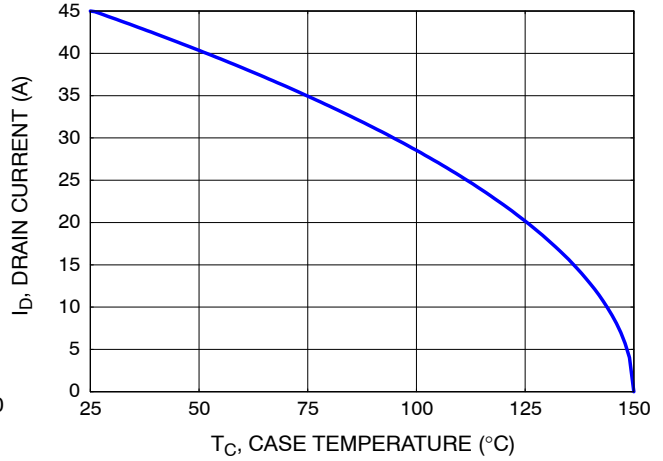Figure 8. On−Resistance Variation vs. Temperature

Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature
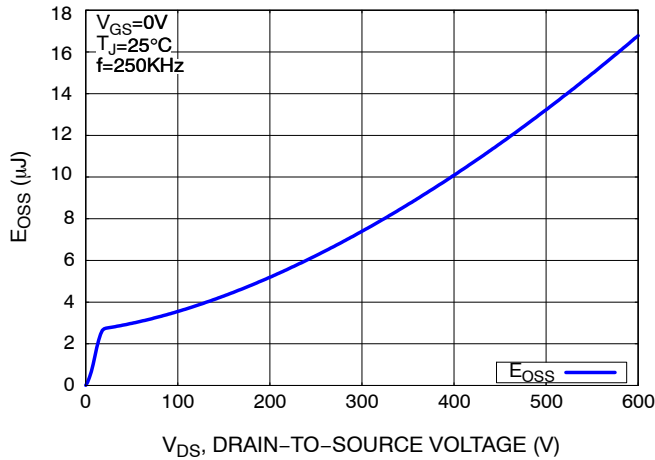
Figure 11. E$_{OSS}$ vs. Drain−to−Source Voltage

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TYPICAL CHARACTERISTICS
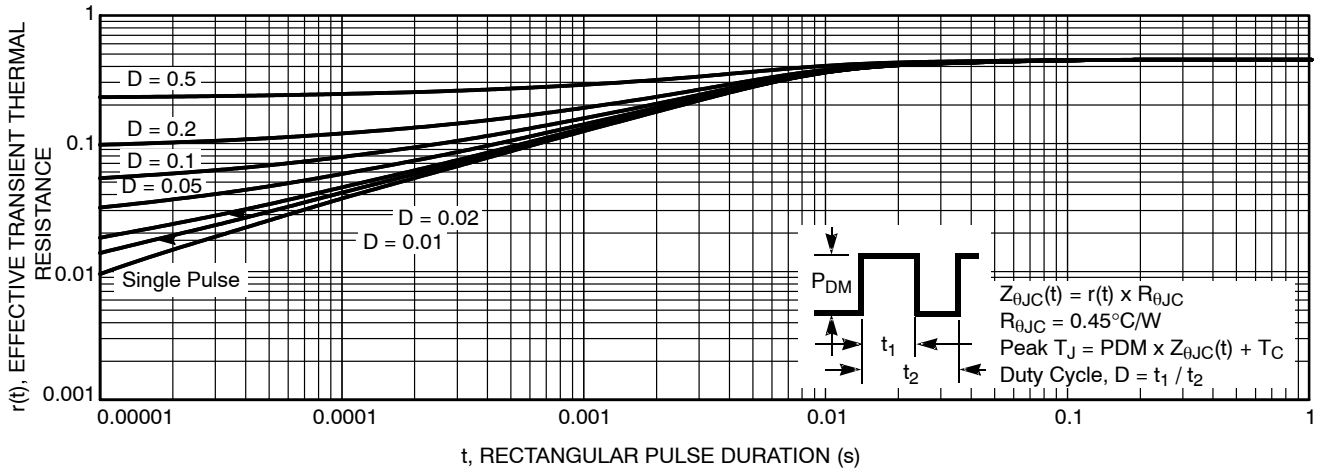
Figure 12. Transient Thermal Impedance

Figure 13. Gate Charge Test Circuit & Waveform
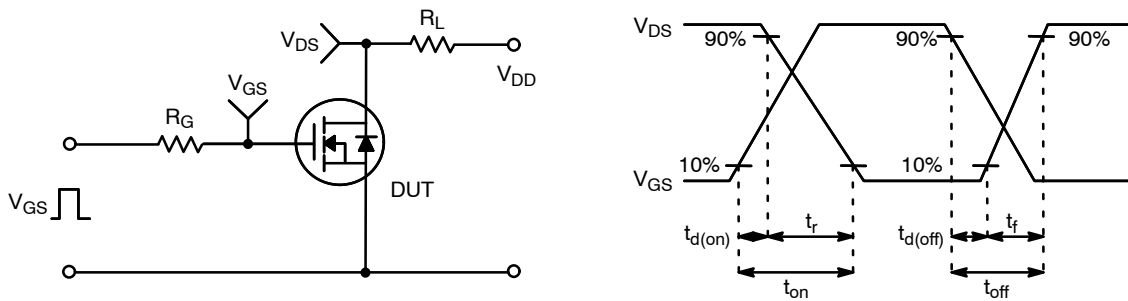
Figure 14. Resistive Switching Test Circuit & Waveforms
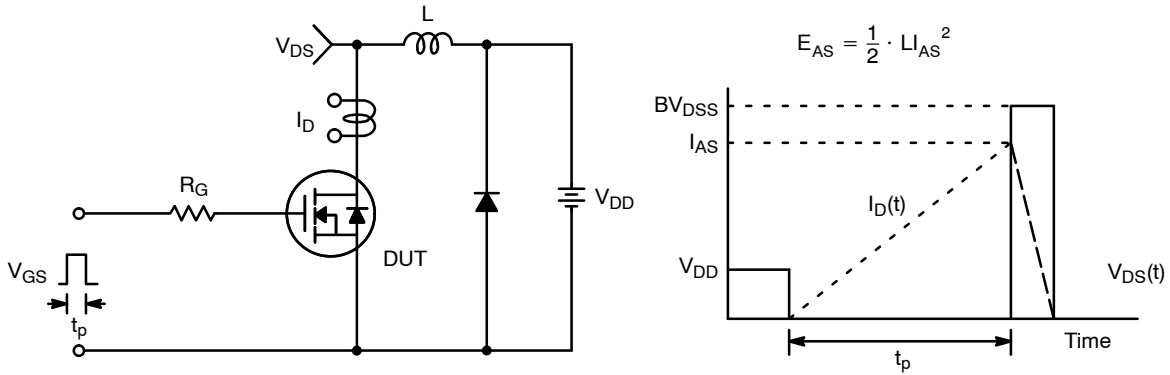
Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms
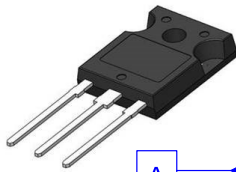
TO−247−3LD
CASE 340CX
ISSUE A

DATE 06 JUL 2020
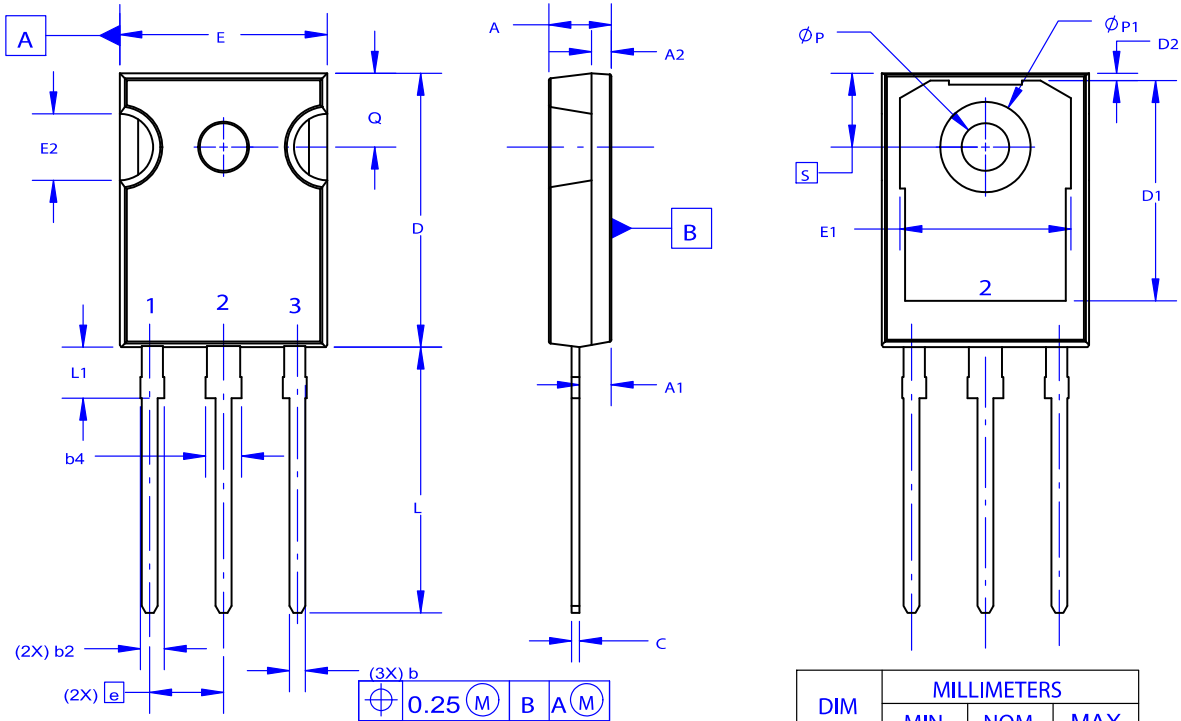
NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
   FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC
MARKING DIAGRAM*

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to
device data sheet for actual part marking.
Pb−Free indicator, "G" or microdot " ▪ ", may
or may not be present. Some products may
not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
⌀P	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
⌀P1	6.60	6.80	7.00

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ADDITIONAL INFORMATION

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